

C.U.SHAH UNIVERSITY

Winter Examination-2015

Subject Name: Semiconductor Memories Design

Subject Code: 5TE03SMD1

Branch: M.Tech (VLSI and Embedded Systems Design)

Semester: 3

Date: 22/12/2015

Time: 2:30 To 5:30

Marks: 70

Instructions:

- (1) Use of Programmable calculator and any other electronic instrument is prohibited.
 - (2) Instructions written on main answer book are strictly to be obeyed.
 - (3) Draw neat diagrams and figures (if necessary) at right places.
 - (4) Assume suitable data if needed.
-

SECTION – I

- Q-1 Attempt the Following questions (07)**
- a. Define static noise margin.
 - b. What is scaling of SRAM?
 - c. Define Redundancy in SRAM Design.
 - d. What is importance of Sense Amplifier in SRAM?
 - e. What are the disadvantages of 4T-SRAM Cell with Polysilicon Resistor Load?
 - f. What are differences between 6T SRAM cell and 4T Loadless SRAM Cell?
 - g. What is the function of Pre-charge circuit in SRAM?

- Q-2 Attempt all questions (14)**
- (a) Explain the Moore's Law of semiconductor memories.
 - (b) Draw and explain the Six-Transistor (6T) CMOS SRAM Cell.

OR

- Q-2 Attempt all questions (14)**
- (a) Draw and explain the Four-Transistor (4T) Loadless SRAM Cell.
 - (b) Draw and explain the typical circuit with a current-mirror type sense amplifier, a PRL SRAM cell and precharge/load transistors.

- Q-3 Attempt all questions (14)**
- (a) Explain with the help of block diagram Delay-Line Based Timing Control method used in SRAMs.
 - (b) Draw and explain the circuit diagram of the 4-1 pass-transistor column decoder with a predecoder.

OR

- Q-3 Attempt all questions (14)**
- (a) Explain with the help of circuit diagram the Address Transition Detector (ATD).
 - (b) Explain with the help of block diagram Replica-Loop Based Timing Control



method used in SRAMs.

SECTION – II

- Q-4** **Attempt the Following questions** **(07)**
- a. What is latency time of DRAM?
 - b. What do you mean by refresh cycle?
 - c. What is digitline pitch?
 - d. What is wordline pitch?
 - e. What is rate of activation?
 - f. What are the disadvantages of open digitline array architecture?
 - g. What are the advantages of folded digitline array architecture?

- Q-5** **Attempt all questions** **(14)**
- (a) Draw and explain 3-transistor DRAM cell.
 - (b) Write a note on Multiple Memory Arrays.

OR

- Q-5** **Attempt all questions** **(14)**
- (a) Draw and explain the functional block diagram of 1K-bit DRAM.
 - (b) Enlist the Modes of operation of DRAM. Explain with the help of timing diagram Page Mode.

- Q-6** **Attempt all questions** **(14)**
- (a) What is the importance of Equilibration and Bias Circuits in DRAM? Explain.
 - (b) Draw and explain Bilevel Digitline Array Architecture Schematic.

OR

- Q-6** **Attempt all Questions** **(14)**
- (a) Draw and explain basic circuit of Nsense and Psense Amplifiers.
 - (b) Draw and explain the basic circuit of Bootstrap Wordline Driver.

